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Toshiba Semiconductor & Storage TPCC8006-H(TE12LQM

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### **TPCC8006-H**

TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOS -H)

# ТРСС8006-Н

High-Efficiency DC-DC Converter Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: Q<sub>SW</sub> = 7.4 nC (typ.)
- Low drain-source ON-resistance:

 $R_{DS(ON)} = 6.5 \text{ m}\Omega \text{ (typ.)} (V_{GS} = 4.5 \text{ V})$ 

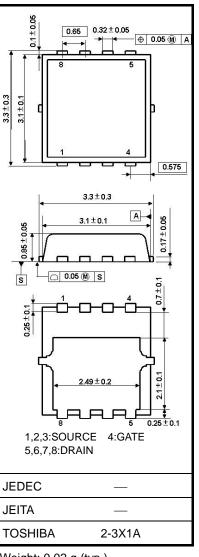
- High forward transfer admittance:  $|Y_{fs}| = 67 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 30 \ V)$
- Enhancement mode: V\_{th} = 1.3 to 2.3 V (V\_{DS} = 10 V, I\_{D} = 0.2 mA)

#### Absolute Maximum Ratings (Ta = 25°C)

Characte	eristic	Symbol	Rating	Unit
Drain-source voltage		V <sub>DSS</sub>	30	V
Drain-gate voltage (R	k <sub>GS</sub> = 20 kΩ)	V <sub>DGR</sub>	30	V
Gate-source voltage		V <sub>GSS</sub>	±20	V
Drain current	DC (Note 1)	I <sub>D</sub>	22	А
Drain current	Pulsed (Note 1)	I <sub>DP</sub>	66	A
Drain power dissipati	on (Tc = 25 )	PD	27	W
Drain power dissipati	on (t = 10 s) (Note 2a)	PD	1.9	W
Drain power dissipati	on (t = 10 s) (Note 2b)	PD	0.7	W
Single-pulse avalanc	he energy (Note 3)	E <sub>AS</sub>	126	mJ
Avalanche current		I <sub>AR</sub>	22	А
Repetitive avalanche (To	energy c = 25 ) (Note 4)	E <sub>AR</sub>	1.89	mJ
Channel temperature	•	T <sub>ch</sub>	150	°C
Storage temperature	range	T <sub>stg</sub>	-55 to 150	°C

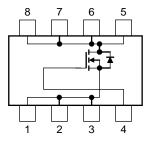
Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



Weight: 0.02 g (typ.)

### **Circuit Configuration**



This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm



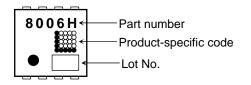
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#### **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case $(Tc = 25)$	R <sub>th (ch-c)</sub>	4.7	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R <sub>th (ch-a)</sub>	66	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	180	°C/W

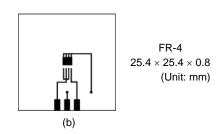
#### Marking (Note 5)



Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

FR-4 25.4 × 25.4 × 0.8 (Unit: mm) (a)

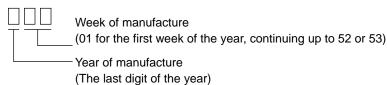


(b) Device mounted on a glass-epoxy board (b)

Note 3:  $V_{DD} = 24 \text{ V}, \text{ T}_{ch} = 25^{\circ}\text{C}$  (initial), L = 200  $\mu$ H, R<sub>G</sub> = 25  $\Omega$ , I<sub>AR</sub> = 22 A

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: \* Weekly code: (Three digits)





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### **Electrical Characteristics (Ta = 25°C)**

Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	rrent	I <sub>GSS</sub>	$V_{GS}=\pm 20~V,~V_{DS}=0~V$		_	±100	nA
Drain cutoff curre	ent	I <sub>DSS</sub>	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$		_	10	μA
Drain-source breakdown voltage		V (BR) DSS	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	30	— — <sub>—</sub>	v	
Drain-source bre	akuown vollage	V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15	_		v
Gate threshold v	ate threshold voltage		$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 0.2 \text{ mA}$	1.3	_	2.3	V
Drain-source ON	ragistance	Pre (eu)	$V_{GS} = 4.5 \text{ V}, I_D = 11 \text{ A}$	_	6.5	9.3	mΩ
Diam-source ON	-resistance	R <sub>DS (ON)</sub>	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 11 \text{ A}$	_	5.3	8.0	
Forward transfer	admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 11 A	34	67	_	S
Input capacitance	Э	C <sub>iss</sub>		_	1700	2200	pF
Reverse transfer	capacitance	C <sub>rss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	110	180	
Output capacitance		C <sub>oss</sub>			350		
Gate resistance		rg	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ f} = 5 \text{ MHz}$	_	2.8	4.2	Ω
Switching time	Rise time	tr	$V_{GS} \stackrel{10}{\overset{0}{}_{0}} V \prod_{i = 1}^{i = 11} I_{i} A$	_	3.8	_	ns
	Turn-on time	t <sub>on</sub>		_	10	_	
	Fall time	t <sub>f</sub>		_	9.7	_	
	Turn-off time	t <sub>off</sub>		_	42	_	
Total gate charge		Qg	$V_{DD} \approx 24 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 22 \text{ A}$		27		
(gate-source plus	gate-source plus gate-drain)		$V_{DD}\approx 24~V,~V_{GS}=5~V,~I_{D}=22~A$		15		
Gate-source charge 1		Q <sub>gs1</sub>	$V_{DD} \approx 24$ V, $V_{GS} = 10$ V, $I_D = 22$ A		5.2		nC
Gate-drain ("Miller") charge		Q <sub>gd</sub>			4.8		
Gate switch char	ge	Q <sub>SW</sub>			7.4	—	

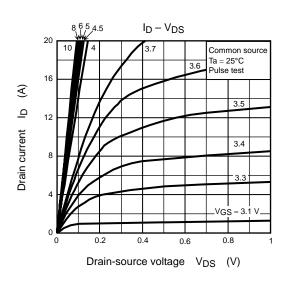
### Source-Drain Ratings and Characteristics (Ta = 25°C)

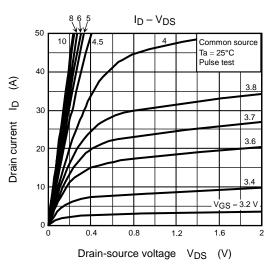
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I <sub>DRP</sub>	—	_	_	66	А
Forward voltage (diode)			V <sub>DSF</sub>	$I_{DR} = 22 \text{ A}, V_{GS} = 0 \text{ V}$		_	-1.2	V

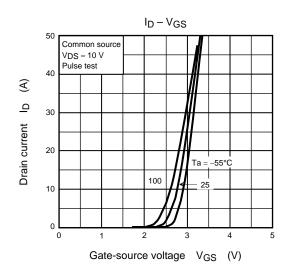


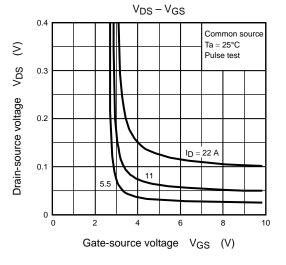
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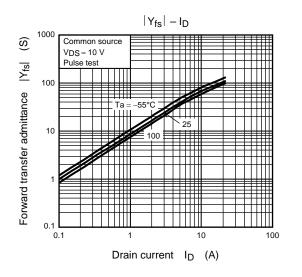
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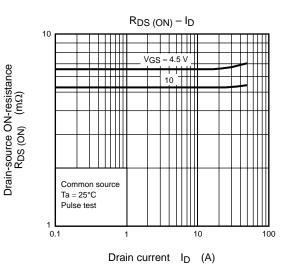










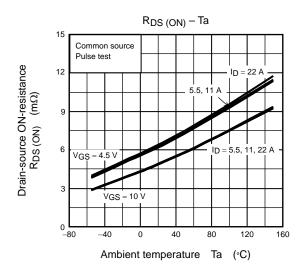


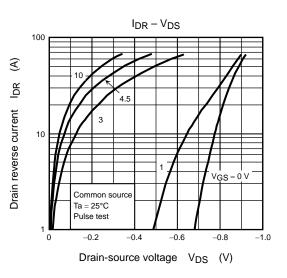
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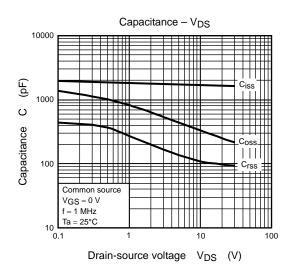


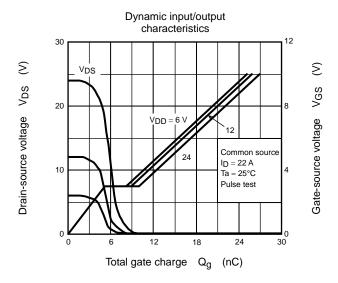
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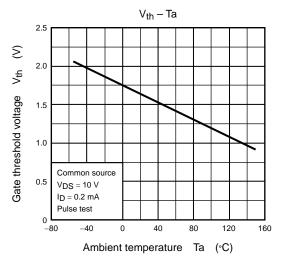
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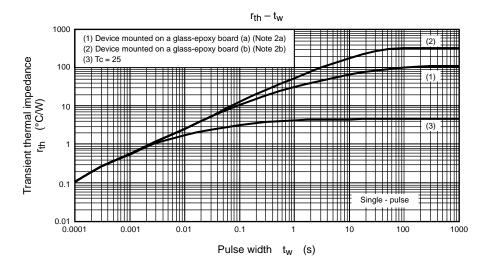




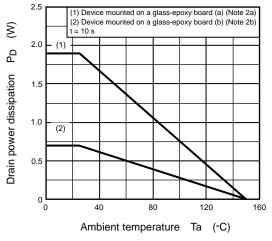


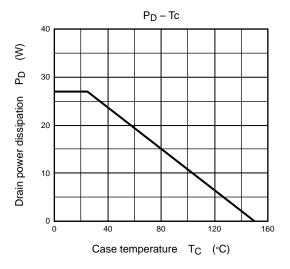
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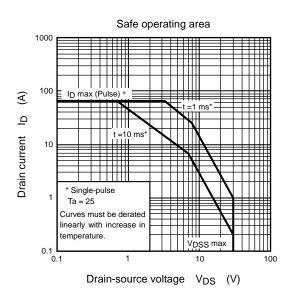
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